

RELIABILITY REPORT
FOR
MAX8508ETE
PLASTIC ENCAPSULATED DEVICES

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MAXIM INTEGRATED PRODUCTS

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Conclusion

The MAX8508 successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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I. Device Description

A. General

The MAX8508 integrates a PWM step-down DC-DC regulator and a 75mΩ (typ) bypass FET to power the PA in WCDMA and cdmaOne™ cell phones. The supply voltage range is from 2.6V to 5.5V, and the guaranteed output current is 600mA. One megahertz PWM switching allows for small external components.

The MAX8508 is externally programmed for fixed 0.75V to 3.4V output. Digital logic enables a high-power (HP) bypass mode that connects the output directly to the battery for all versions. The MAX8508 is designed so the output settles in less than 30μs for a full-scale change in output voltage and load current.

The MAX8508 are offered in 16-pin 4mm x 4mm thin QFN packages (0.8mm max height).

B. Absolute Maximum Ratings

<u>Item</u>	<u>Rating</u>
BATTP, BATT, OUT, SHDN, SKIP, HP, REFIN, FB to GND	-0.3V to +6V
PGND to GND	-0.3V to +0.3V
BATT to BATTP	-0.3V to +0.3V
OUT, COMP, REF to GND	-0.3V to (VBATT + 0.3V)
LX Current (Note 1)	1.6A
OUT Current (Note 1)	3.2A
Output Short-Circuit Duration	Continuous
Operating Temperature Range	-40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C
Continuous Power Dissipation (TA = +70°C)	
16-Pin Thin QFN	1349mW
Derates above +70°C	
16-Pin Thin QFN	16.9mW/°C

II. Manufacturing Information

- A. Description/Function: PWM Step-Down DC-DC Converters with 75 Ohm Bypass FET for WCDMA and cdmaOne Handsets
- B. Process: B8 (Standard 0.8 micron silicon gate CMOS)
- C. Number of Device Transistors: 2020
- D. Fabrication Location: California, USA
- E. Assembly Location: Thailand
- F. Date of Initial Production: July, 2003

III. Packaging Information

- A. Package Type: **16-Pin Thin QFN (4x4)**
- B. Lead Frame: Copper
- C. Lead Finish: Solder Plate
- D. Die Attach: Silver-Filled Epoxy
- E. Bondwire: Gold (1.3 mil dia.)
- F. Mold Material: Epoxy with silica filler
- G. Assembly Diagram: # 05-9000-0594
- H. Flammability Rating: Class UL94-V0
- I. Classification of Moisture Sensitivity per JEDEC standard JESD22-112: Level 1

IV. Die Information

- A. Dimensions: 88 x 88 mils
- B. Passivation: $\text{Si}_3\text{N}_4/\text{SiO}_2$ (Silicon nitride/ Silicon dioxide)
- C. Interconnect: Aluminum/Si (Si = 1%)
- D. Backside Metallization: None
- E. Minimum Metal Width: 0.8 microns (as drawn)
- F. Minimum Metal Spacing: 0.8 microns (as drawn)
- G. Bondpad Dimensions: 5 mil. Sq.
- H. Isolation Dielectric: SiO_2
- I. Die Separation Method: Wafer Saw

V. Quality Assurance Information

- A. Quality Assurance Contacts: Jim Pedicord (Manager, Reliability Operations)
Bryan Preeshl (Executive Director)
Kenneth Huening (Vice President)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in **Table 1**. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4389 \times 48 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

Temperature Acceleration factor assuming an activation energy of 0.8eV

$$\lambda = 22.62 \times 10^{-9}$$

$$\lambda = 22.62 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

This low failure rate represents data collected from Maxim's reliability monitor program. In addition to routine production Burn-In, Maxim pulls a sample from every fabrication process three times per week and subjects it to an extended Burn-In prior to shipment to ensure its reliability. The reliability control level for each lot to be shipped as standard product is 59 F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on any lot that exceeds this reliability control level. Attached Burn-In Schematic (Spec. # 06-6164) shows the static Burn-In circuit. Maxim also performs quarterly 1000 hour life test monitors. This data is published in the Product Reliability Report (**RR-1M**).

B. Moisture Resistance Tests

Maxim pulls pressure pot samples from every assembly process three times per week. Each lot sample must meet an LTPD = 20 or less before shipment as standard product. Additionally, the industry standard 85°C/85%RH testing is done per generic device/package family once a quarter.

C. E.S.D. and Latch-Up Testing

The PM98-2 die type has been found to have all pins able to withstand a transient pulse of $\pm 1500\text{V}$, per Mil-Std-883 Method 3015 (reference attached ESD Test Circuit). Latch-Up testing has shown that this device withstands a current of $\pm 250\text{mA}$.

Table 1
Reliability Evaluation Test Results

MAX8508ETE

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	PACKAGE	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Test (Note 1)					
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality		48	0
Moisture Testing (Note 2)					
Pressure Pot	Ta = 121°C P = 15 psi. RH= 100% Time = 168hrs.	DC Parameters & functionality	QFN	77	0
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality		77	0
Mechanical Stress (Note 2)					
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters		77	0

Note 1: Life Test Data may represent plastic DIP qualification lots.

Note 2: Generic Package/Process data

Attachment #1

TABLE II. Pin combination to be tested. 1/ 2/

	Terminal A (Each pin individually connected to terminal A with the other floating)	Terminal B (The common combination of all like-named pins connected to terminal B)
1.	All pins except V_{PS1} 3/	All V_{PS1} pins
2.	All input and output pins	All other input-output pins

1/ Table II is restated in narrative form in 3.4 below.

2/ No connects are not to be tested.

3/ Repeat pin combination 1 for each named Power supply and for ground

(e.g., where V_{PS1} is V_{DD} , V_{CC} , V_{SS} , V_{BB} , GND, $+V_S$, $-V_S$, V_{REF} , etc).

3.4 Pin combinations to be tested.

- a. Each pin individually connected to terminal A with respect to the device ground pin(s) connected to terminal B. All pins except the one being tested and the ground pin(s) shall be open.
- b. Each pin individually connected to terminal A with respect to each different set of a combination of all named power supply pins (e.g., V_{SS1} , or V_{SS2} or V_{SS3} or V_{CC1} , or V_{CC2}) connected to terminal B. All pins except the one being tested and the power supply pin or set of pins shall be open.
- c. Each input and each output individually connected to terminal A with respect to a combination of all the other input and output pins connected to terminal B. All pins except the input or output pin being tested and the combination of all the other input and output pins shall be open.



